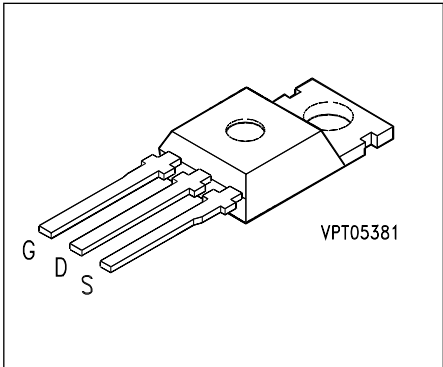


SIPMOS® Power Transistors

- N channel
- Enhancement mode

BUZ 80
BUZ 80 A



Type	V_{DS}	I_D	$R_{DS(on)}$	Package ¹⁾	Ordering Code
BUZ 80	800 V	2.6 A	4.0 Ω	TO-220 AB	C67078-A1309-A2
BUZ 80 A	800 V	3.0 A	3.0 Ω	TO-220 AB	C67078-A1309-A3

Maximum Ratings

Parameter	Symbol	BUZ		Unit
		80	80 A	
Continuous drain current, $T_C = 50\text{ °C}$	I_D	2.6	3.0	A
Pulsed drain current, $T_C = 25\text{ °C}$	$I_{D\text{ puls}}$	10	12	
Drain-source voltage	V_{DS}	800		V
Drain-gate voltage, $R_{GS} = 20\text{ k}\Omega$	V_{DGR}	800		
Gate-source voltage	V_{GS}	± 20		
Power dissipation, $T_C = 25\text{ °C}$	P_{tot}	75		W
Operating and storage temperature range	T_j, T_{stg}	- 55 ... + 150		°C
Thermal resistance, chip-case	$R_{th\text{ JC}}$	$\leq$ 1.67		K/W
DIN humidity category, DIN 40 040	—	E		—
IEC climatic category, DIN IEC 68-1	—	55/150/56		

1) See chapter Package Outlines.

Electrical Characteristics

at $T_j = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static characteristics

Drain-source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$	$V_{(BR) DSS}$	800	–	–	V
Gate threshold voltage $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$	$V_{GS(th)}$	2.1	3.0	4.0	
Zero gate voltage drain current $V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	I_{DSS}	– –	20 100	250 1000	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	–	10	100	nA
Drain-source on-resistance $V_{GS} = 10\text{ V}$, $I_D = 1.5\text{ A}$ BUZ 80 BUZ 80 A	$R_{DS(on)}$	– –	3.5 2.7	4.0 3.0	Ω

Dynamic characteristics

Forward transconductance $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$ $I_D = 1.5\text{ A}$	g_{fs}	1.0	1.8	–	S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	–	1600	2100	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	–	90	150	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	–	30	55	
Turn-on time t_{on} , ($t_{on} = t_{d(on)} + t_r$) $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3.0\text{ A}$, $R_{GS} = 50\text{ Ω}$	$t_{d(on)}$	–	30	45	ns
	t_r	–	40	60	
Turn-off time t_{off} , ($t_{off} = t_{d(off)} + t_f$) $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3.0\text{ A}$, $R_{GS} = 50\text{ Ω}$	$t_{d(off)}$	–	110	140	
	t_f	–	60	80	

Electrical Characteristics (cont'd)

at $T_j = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

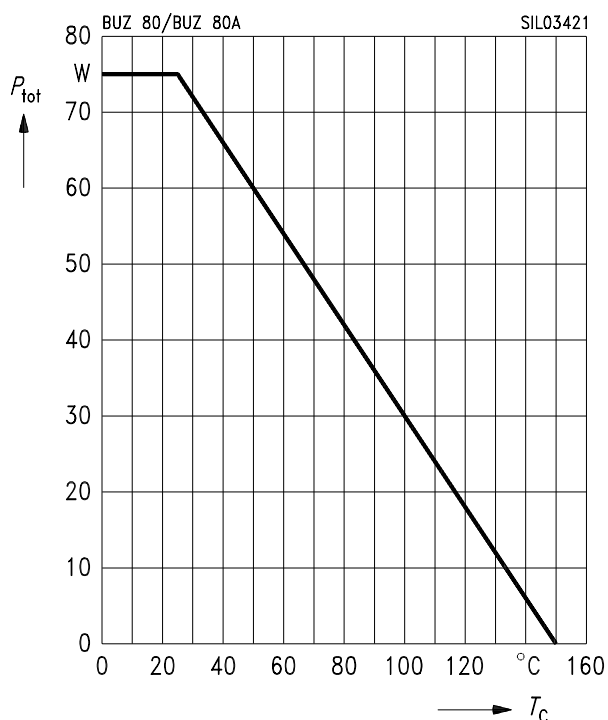
Reverse diode

Continuous reverse drain current $T_C = 25\text{ °C}$ BUZ 80 BUZ 80 A	I_S	— —	— —	2.6 3.0	A
Pulsed reverse drain current $T_C = 25\text{ °C}$ BUZ 80 BUZ80 A	I_{SM}	— —	— —	10 12	
Diode forward on-voltage $I_S = 6.0\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	—	1.05	1.3	V
Reverse recovery time $V_R = 100\text{ V}$, $I_F = I_S$, $di_F / dt = 100\text{ A}/\mu\text{s}$	t_{rr}	—	1.8	—	μs
Reverse recovery charge $V_R = 100\text{ V}$, $I_F = I_S$, $di_F / dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	—	12	—	μC

Characteristics at $T_j = 25^\circ\text{C}$, unless otherwise specified.

Total power dissipation

$$P_{\text{tot}} = f(T_c)$$

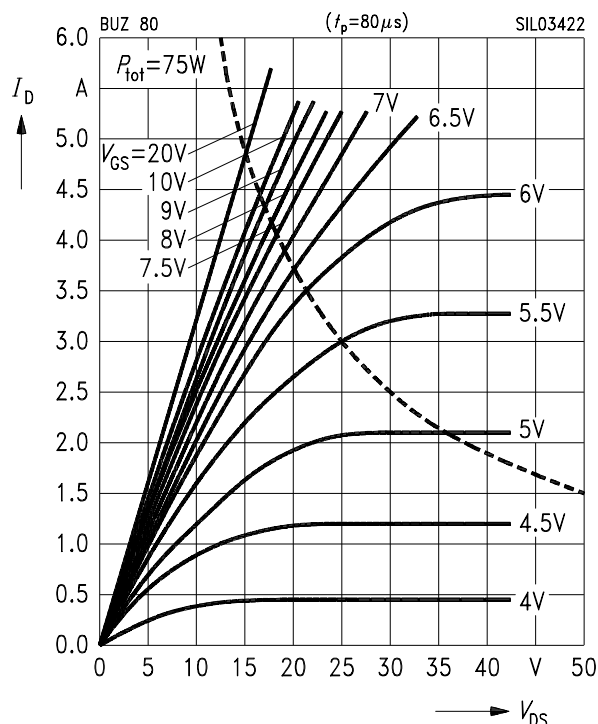


Typ. output characteristics

$$I_D = f(V_{\text{DS}})$$

parameter: $t_p = 80 \mu\text{s}$

BUZ 80

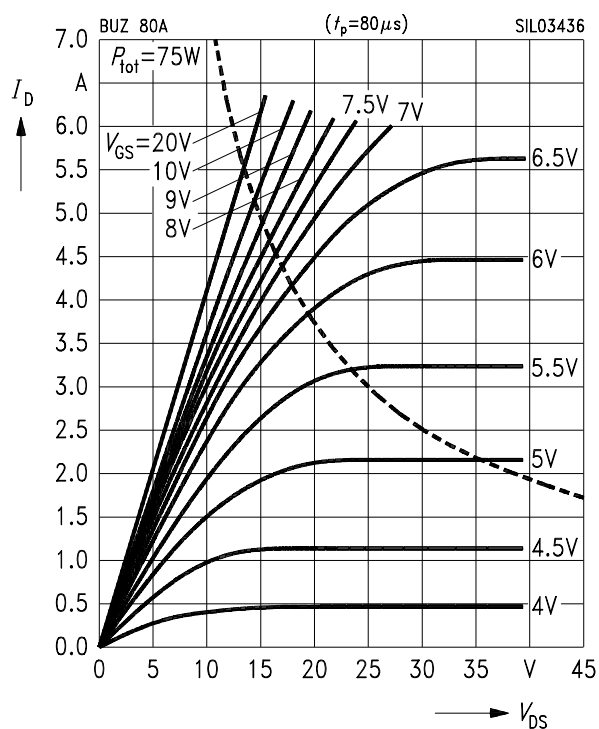


Typ. output characteristics

$$I_D = f(V_{\text{DS}})$$

parameter: $t_p = 80 \mu\text{s}$

BUZ 80 A

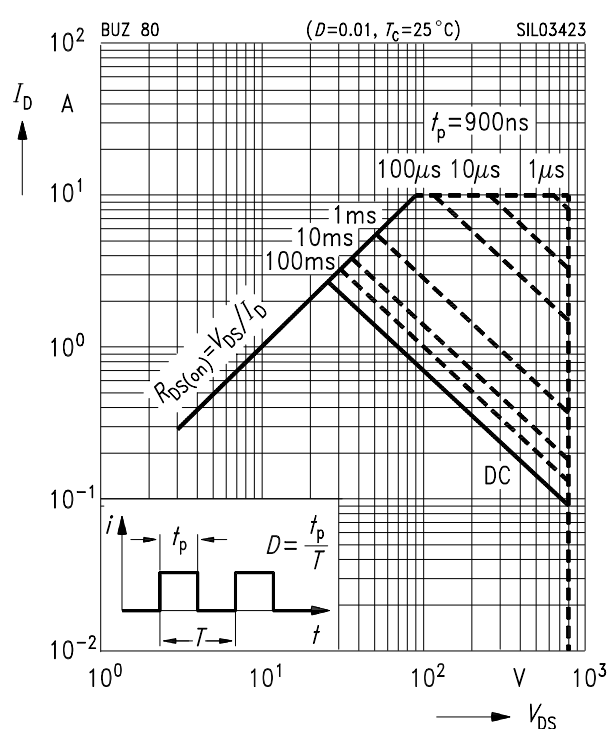


Safe operating area

$$I_D = f(V_{\text{DS}})$$

parameter: $D = 0.01$, $T_c = 25^\circ\text{C}$

BUZ 80

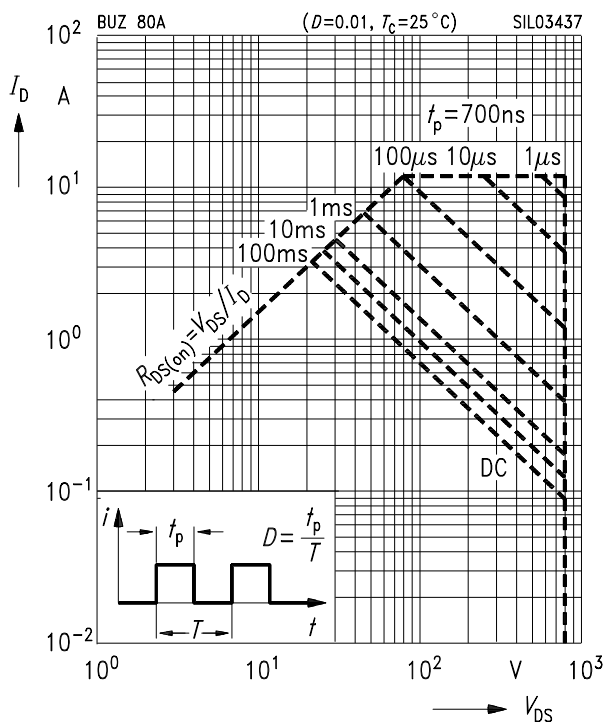


Safe operating area

$$I_D = f(V_{DS})$$

BUZ 80 A

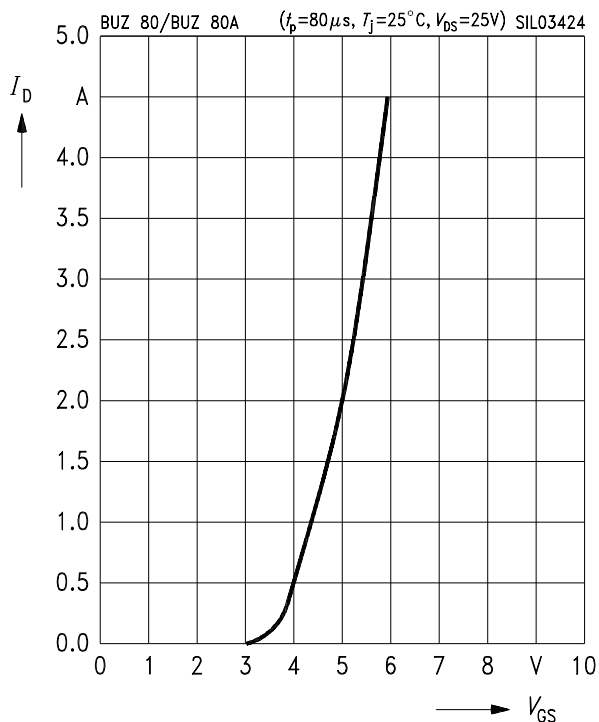
parameter: $D = 0.01$, $T_C = 25^\circ\text{C}$



Typ. transfer characteristics

$$I_D = f(V_{GS})$$

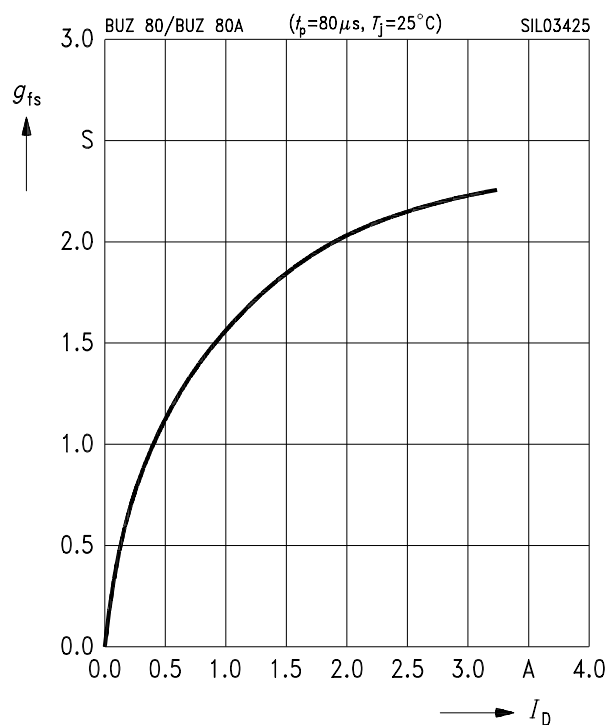
parameter: $t_p = 80\ \mu\text{s}$, $V_{DS} = 25\ \text{V}$



Typ. forward transconductance

$$g_{fs} = f(I_D)$$

parameter: $t_p = 80\ \mu\text{s}$

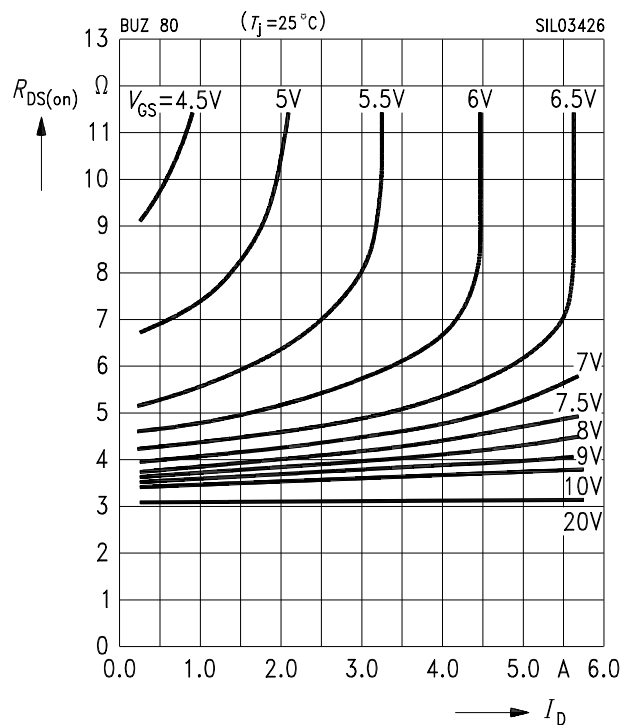


Typ. drain-source on-resistance

$$R_{DS(on)} = f(I_D)$$

BUZ 80

parameter: V_{GS}

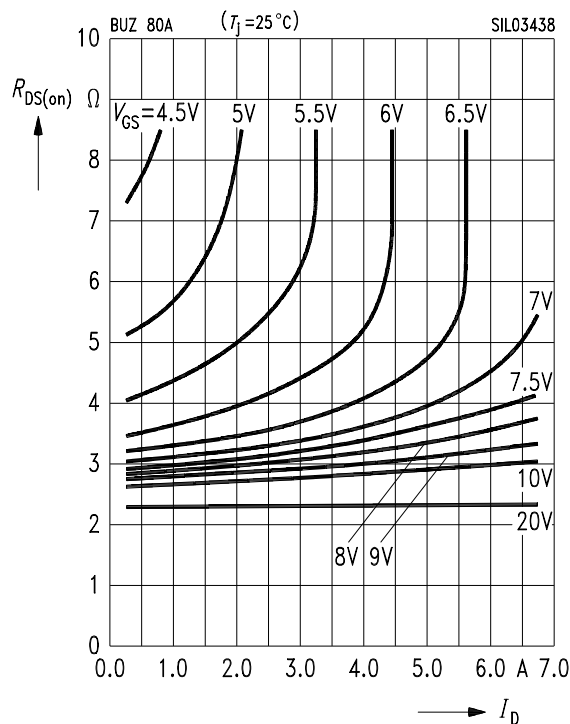


Typ. drain-source on-resistance

$$R_{DS(on)} = f(I_D)$$

BUZ 80 A

parameter: V_{GS}

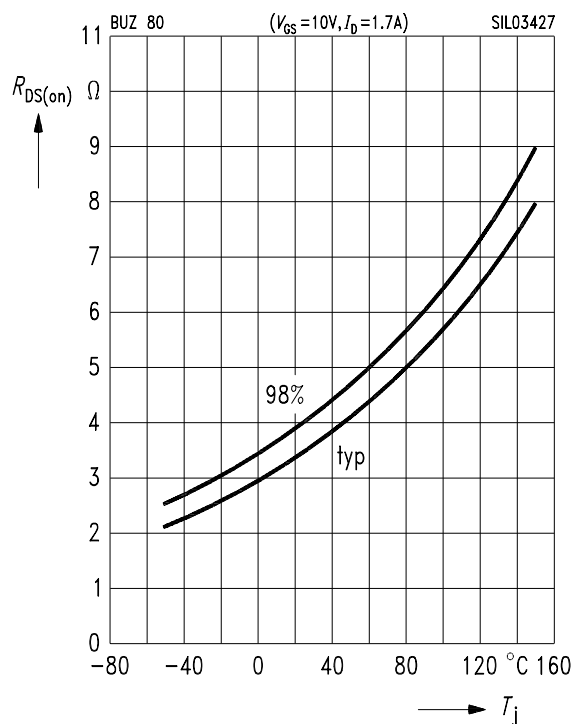


Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

BUZ 80

parameter: $I_D = 1.7\text{ A}$, $V_{GS} = 10\text{ V}$, (spread)

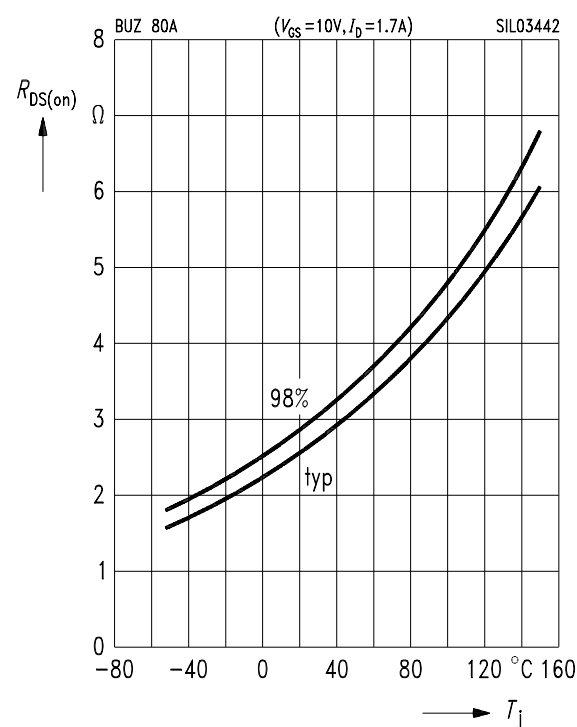


Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

BUZ 80 A

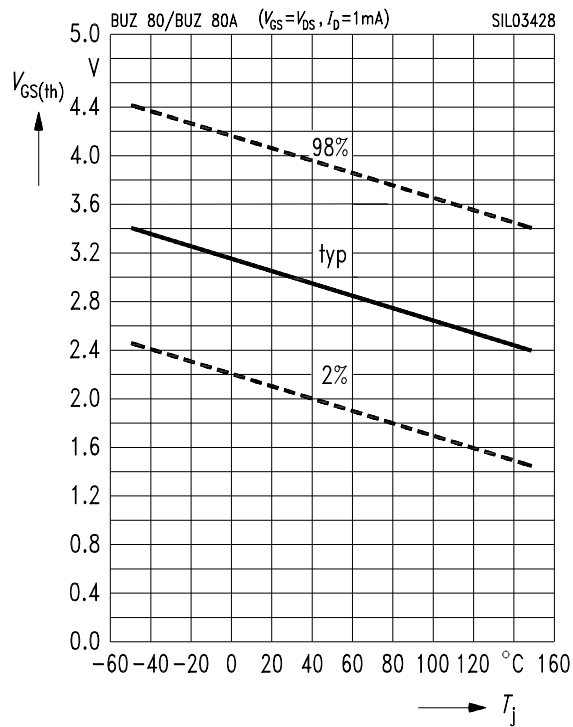
parameter: $I_D = 1.7\text{ A}$, $V_{GS} = 10\text{ V}$, (spread)



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

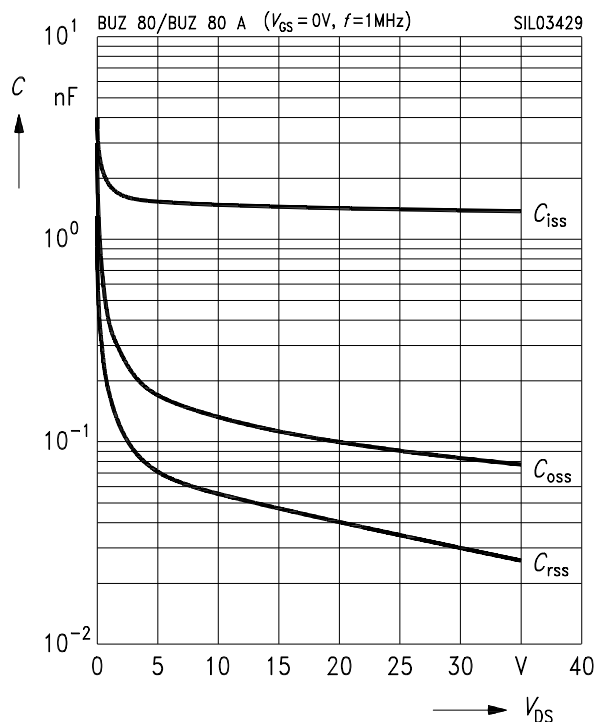
parameter: $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$, (spread)



Typ. capacitances

$$C = f(V_{DS})$$

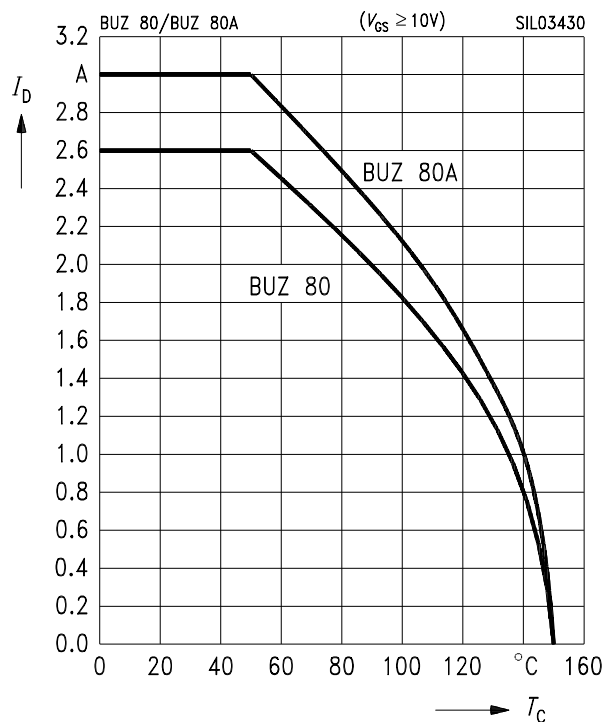
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



Drain current

$$I_D = f(T_C)$$

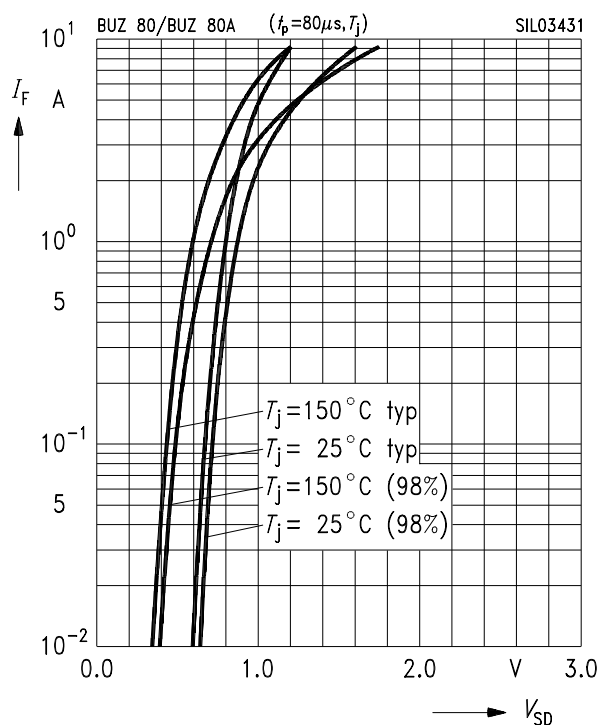
parameter: $V_{GS} \geq 10 \text{ V}$



Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

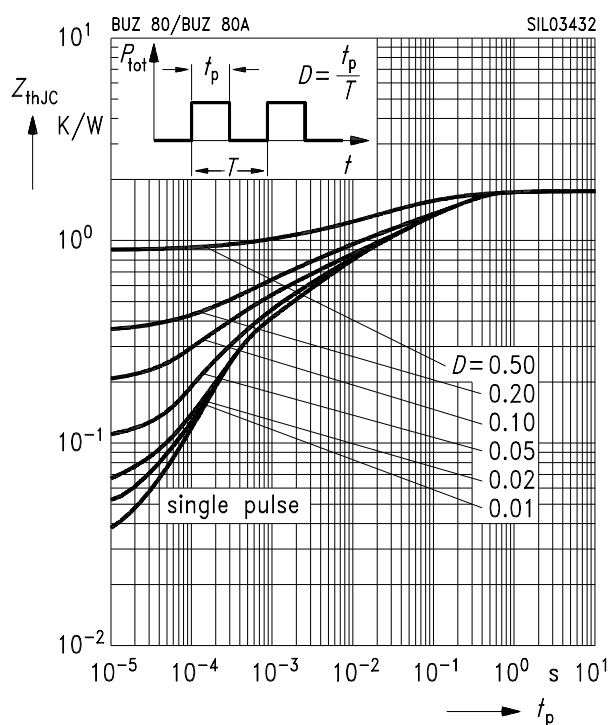
parameter: $t_p = 80 \mu\text{s}$, T_j



Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p / T$



Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

parameter: $I_{D\ puls} = 5\ A$

